

| | Type | Hits | Search Text | DBs |
|---|------|--------|---|--|
| 1 | IS&R | 4 | ((("5384270") or ("5814859")).PN. | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 2 | BRS | 238850 | "438"\$.ccls. (MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 3 | BRS | 104 | S2 and (silicon adj carbide adj MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 4 | BRS | 22 | S3 and (vertical adj MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 5 | BRS | 239138 | "438"\$.ccls. (MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |

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| 6 | BRS | 54 | S5 and (silicon adj carbide adj MOSFET) and (ion adj implantation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 7 | BRS | 2 | S6 and (ion adj implantation adj mask) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 8 | BRS | 34 | S6 and range | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 9 | BRS | 0 | S6 and (ion adj implantation adj range) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 10 | BRS | 239138 | "438"/\$.ccls. (MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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|----|------|-------|---|--|
| 11 | BRS | 0 | S10 and (silicon adj carbide adj MOSFET) and (implantation adj angle) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 12 | BRS | 104 | S10 and (silicon adj carbide adj MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 13 | BRS | 0 | S13 and (angle adj of adj implantation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 14 | BRS | 54 | S12 and (ion adj implantation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |
| 15 | BRS | 36155 | "438"\$.ccls. and (angloe of implantation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |

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|----|------|-------|--|--|
| 16 | BRS | 47516 | "438"/\$.ccls. and (angle of implantation) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 17 | BRS | 0 | S16 and (silicon adj carbide adj MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 18 | BRS | 7447 | S16 and (MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 19 | BRS | 475 | S18 and (SiC) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |
| 20 | BRS | 37 | S19 and (vertical adj MOSFET) | US-PGPUB; USPAT; EPO; JPO; DERVENT; IBM_TDB |